

PN2907A / MMBT2907A / PZT2907A

60 V PNP General-Purpose Transistor

Features

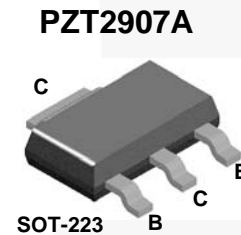
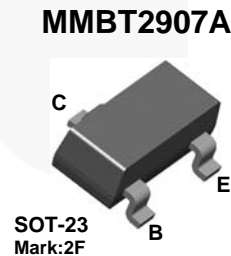
- High DC Current Gain (h_{FE}) Range: 100 ~ 300
- High-Current Gain Bandwidth Product (f_T): 200 MHz (Minimum)
- Maximum Turn-On Time (t_{on}): 45 ns
- Maximum Turn-Off Time (t_{off}): 100 ns
- Ultra-Small Surface-Mount Package: SOT-223 (PZT2907A)

Applications

- General-Purpose Amplifier
- Switch

Description

The PN2907A, MMBT2907A, and PZT2907A are 60 V PNP bipolar transistors designed for use as a general-purpose amplifier or switch in applications that require up to 500 mA. Offered in an ultra-small surface-mount package (SOT-223), the PZT2907A is ideal for space-constrained systems. The NPN complementary types are the PN2222A, MMBT2222A, and PZT2222A; respectively.



Ordering Information

Part Number	Top Mark	Package	Packing Method
PN2907ABU	2907A	TO-92 3L	Bulk
PN2907ATF	2907A	TO-92 3L	Tape and Reel
PN2907ATFR	2907A	TO-92 3L	Tape and Reel
PN2907ATA	2907A	TO-92 3L	Ammo
PN2907ATAR	2907A	TO-92 3L	Ammo
MMBT2907A	2F	SOT-23 3L	Tape and Reel
MMBT2907A_D87Z	2F	SOT-23 3L	Tape and Reel
PZT2907A	2907A	SOT-223 4L	Tape and Reel

Absolute Maximum Ratings^{(1),(2)}

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{CBO}	Collector-Base Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current - Continuous	-800	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Notes:

- These ratings are based on a maximum junction temperature of 150°C .
- These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty cycle operations.

Thermal Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Max.			Unit
		PN2907A ⁽⁴⁾	MMBT2907A ⁽³⁾	PZT2907A ⁽⁴⁾	
P_D	Total Device Dissipation	625	350	1000	mW
	Derate Above 25°C	5.0	2.8	8.0	mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	$^\circ\text{C}/\text{W}$

Notes:

- Device is mounted on FR-4 PCB 1.6 inch X 1.6 inch X 0.06 inch.
- PCB size: FR-4 76 x 114 x 1.57 mm³ (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
Off Characteristics					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ⁽⁵⁾	$I_C = -10\text{ mA}, I_B = 0$	-60		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\text{ }\mu\text{A}, I_E = 0$	-60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\text{ }\mu\text{A}, I_C = 0$	-5.0		V
I_{BL}	Base Cut-Off Current	$V_{CE} = -30\text{ V}, V_{EB} = -0.5\text{ V}$		-50	nA
I_{CEX}	Collector Cut-Off Current	$V_{CE} = -30\text{ V}, V_{EB} = -0.5\text{ V}$		-50	nA
I_{CBO}	Collector Cut-Off Current	$V_{CB} = -50\text{ V}, I_E = 0$		-0.02	μA
		$V_{CB} = -50\text{ V}, I_E = 0, T_A = 150^\circ\text{C}$		-20	
On Characteristics					
h_{FE}	DC Current Gain	$I_C = -0.1\text{ mA}, V_{CE} = -10\text{ V}$	75		
		$I_C = -1.0\text{ mA}, V_{CE} = -10\text{ V}$	100		
		$I_C = -10\text{ mA}, V_{CE} = -10\text{ V}$	100		
		$I_C = -150\text{ mA}, V_{CE} = -10\text{ V}^{(5)}$	100	300	
		$I_C = -500\text{ mA}, V_{CE} = -10\text{ V}^{(5)}$	50		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ⁽⁵⁾	$I_C = -150\text{ mA}, I_B = -15\text{ mA}$		-0.4	V
		$I_C = -500\text{ mA}, I_B = -50\text{ mA}$		-1.6	
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -150\text{ mA}, I_B = -15\text{ mA}^{(5)}$		-1.3	V
		$I_C = -500\text{ mA}, I_B = -50\text{ mA}$		-2.6	
Small Signal Characteristics					
f_T	Current Gain - Bandwidth Product	$I_C = -50\text{ mA}, V_{CE} = -20\text{ V},$ $f = 100\text{ MHz}$	200		MHz
C_{ob}	Output Capacitance	$V_{CB} = -10\text{ V}, I_E = 0,$ $f = 100\text{ kHz}$		8.0	pF
C_{ib}	Input Capacitance	$V_{EB} = -2.0\text{ V}, I_C = 0, f = 100\text{ kHz}$		30	pF
Switching Characteristics					
t_{on}	Turn-On Time	$V_{CC} = -30\text{ V}, I_C = -150\text{ mA},$ $I_{B1} = -15\text{ mA}$		45	ns
t_d	Delay Time			10	ns
t_r	Rise Time			40	ns
t_{off}	Turn-Off Time	$V_{CC} = -6.0\text{ V}, I_C = -150\text{ mA},$ $I_{B1} = I_{B2} = -15\text{ mA}$		100	ns
t_s	Storage Time			80	ns
t_f	Fall Time			30	ns

Notes:

5. Pulse test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2.0\%$.

Typical Performance Characteristics

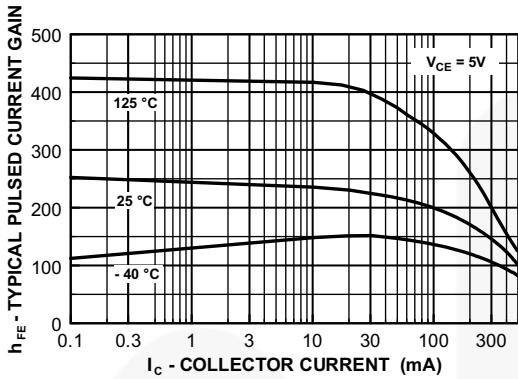


Figure 1. Typical Pulsed Current Gain vs. Collector Current

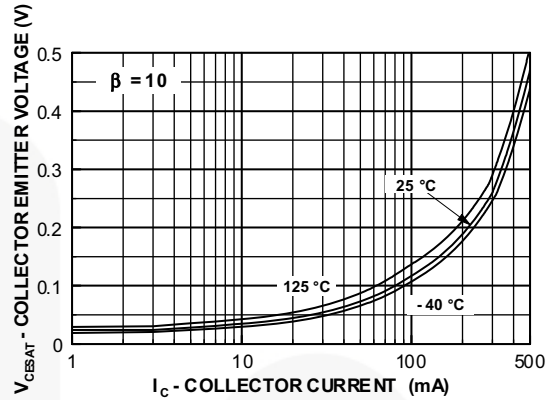


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

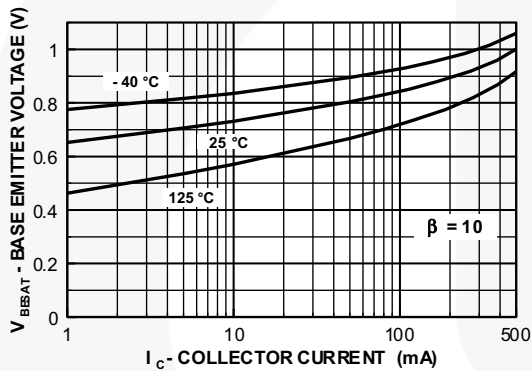


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

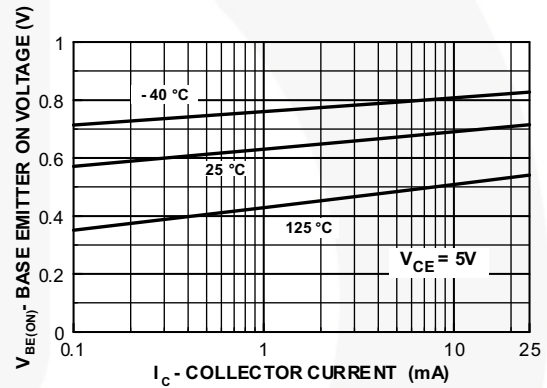


Figure 4. Base-Emitter On Voltage vs. Collector Current

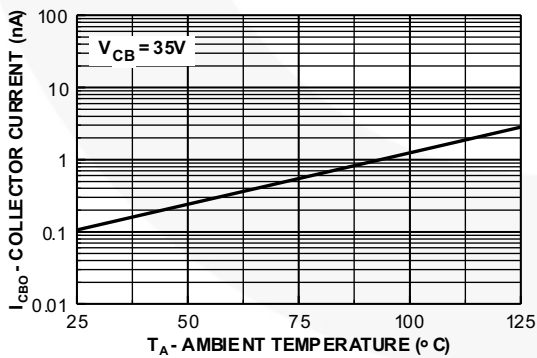


Figure 5. Collector Cut-Off Current vs. Ambient Temperature

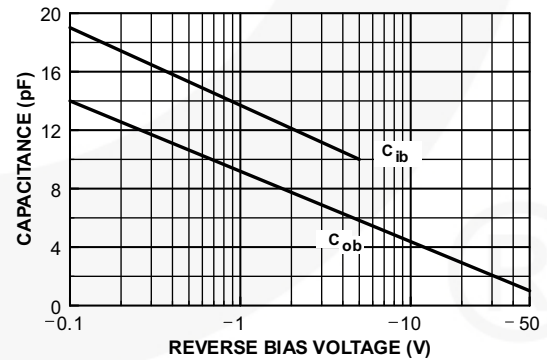


Figure 6. Input and Output Capacitance vs. Reverse Bias Voltage

Typical Performance Characteristics (Continued)

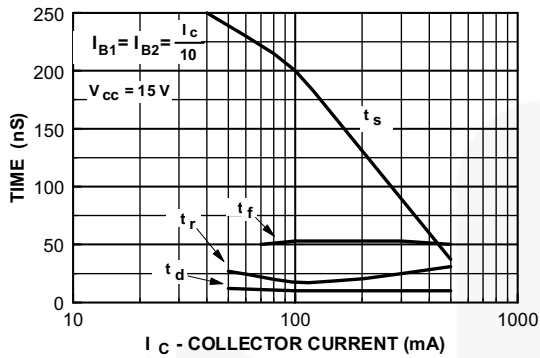


Figure 7. Switching Times vs. Collector Current

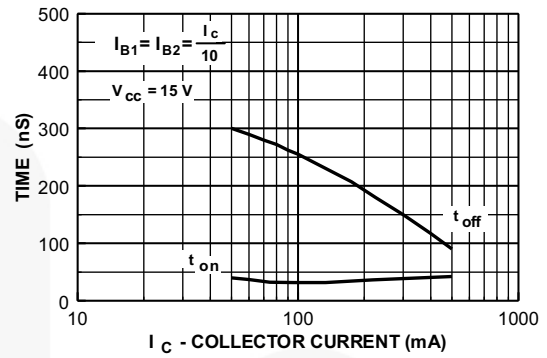


Figure 8. Turn-On and Turn-Off Times vs. Collector Current

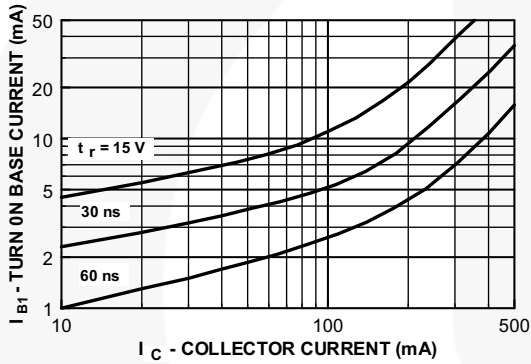


Figure 9. Rise Time vs. Collector and Turn-On Base Currents

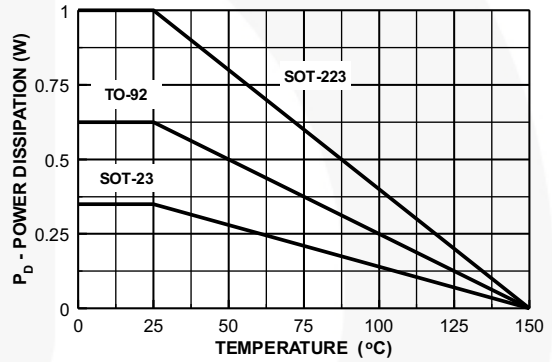


Figure 10. Power Dissipation vs. Ambient Temperature

Typical Performance Characteristics (f = 1.0 kHz)

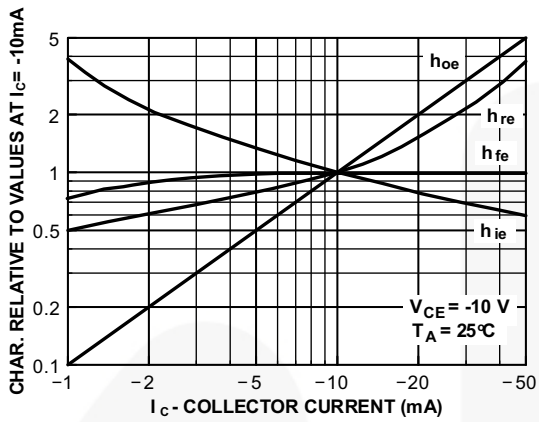


Figure 11. Common Emitter Characteristics

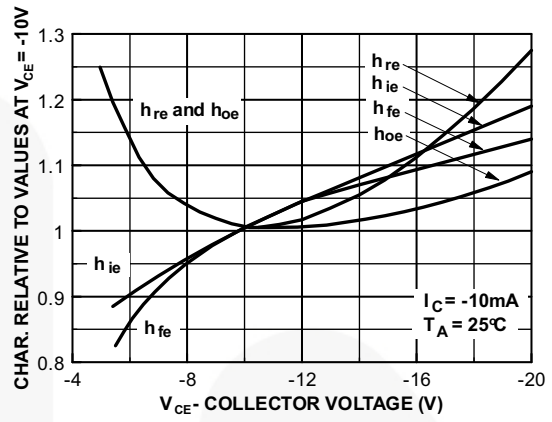


Figure 12. Common Emitter Characteristics

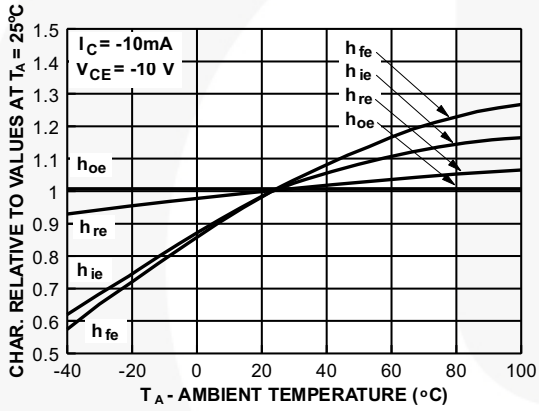
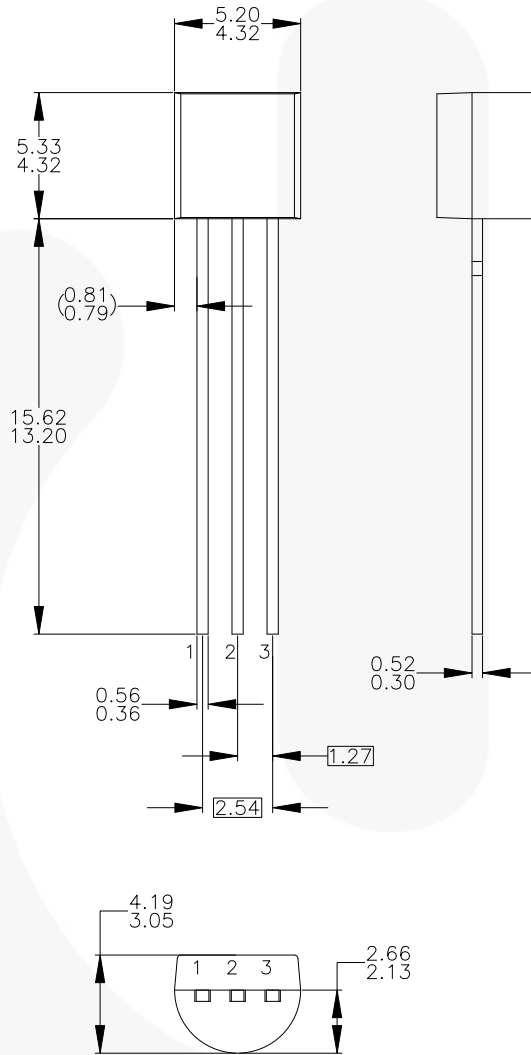


Figure 13. Common Emitter Characteristics

Physical Dimensions

TO-92 (Bulk)



NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994.
- D) TO-92 (92,94,96,97,98) PIN CONFIGURATION:

PIN	92	94	96	97	98
1	E	S	S	E	S
2	B	D	G	C	G
3	C	G	D	B	D

LEGEND:

- P - BIPOLAR
- F - JFET
- M - DMOS
- E - EMITTER
- B - BASE
- C - COLLECTOR
- D - DRAIN
- S - SOURCE
- G - GATE

- E) FOR PACKAGE 92, 94, 96, 97 AND 98: PIN CONFIGURATION DRAIN "D" AND SOURCE "S" ARE INTERCHANGEABLE AT JFET "F" OPTION.
- F) DRAWING FILENAME: MKT-ZA03DREV3.

Figure 14. 3-LEAD, TO92, JEDEC TO-92 COMPLIANT STRAIGHT LEAD CONFIGURATION (OLD TO92AM3) (ACTIVE)

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

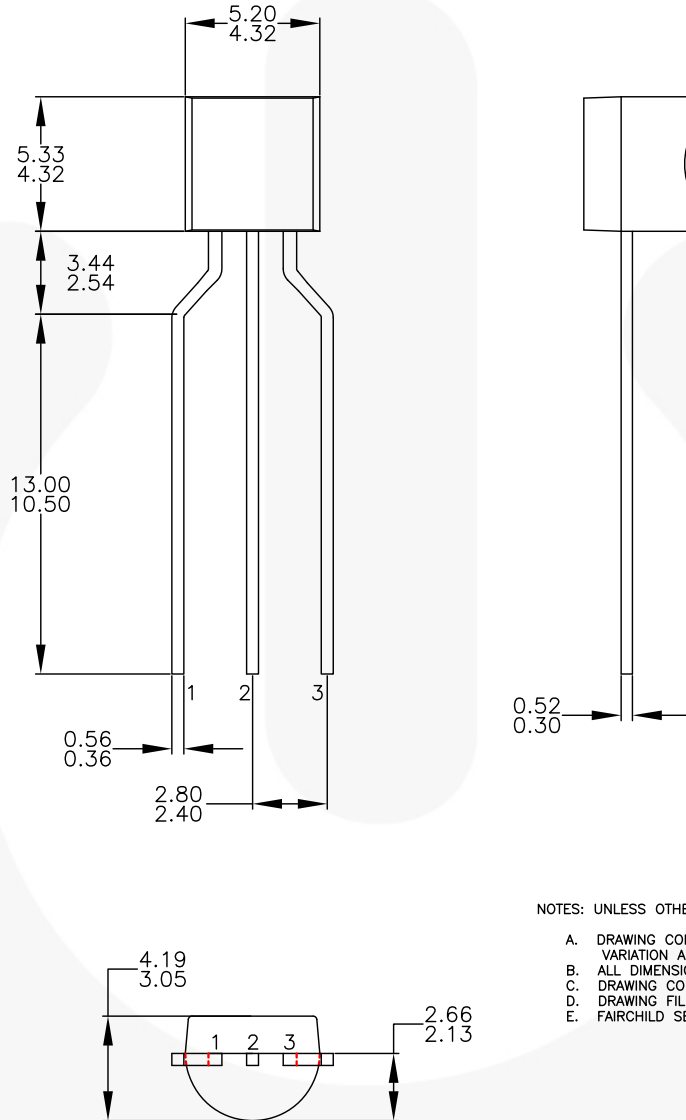
<http://www.fairchildsemi.com/dwg/ZA/ZA03D.pdf>

For current tape and reel specifications, visit Fairchild Semiconductor's online packaging area:

http://www.fairchildsemi.com/packing_dwg/PKG-ZA03D_BK.pdf

Physical Dimensions (Continued)

TO-92 (Tape and Reel, Ammo)



NOTES: UNLESS OTHERWISE SPECIFIED

- A. DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
- D. DRAWING FILENAME: MKT-ZA03FREV3.
- E. FAIRCHILD SEMICONDUCTOR.

Figure 15. 3-LEAD, TO92, MOLDED 0.200 IN LINE SPACING LEAD FORM (J61Z OPTION) (ACTIVE)

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For current tape and reel specifications, visit Fairchild Semiconductor's online packaging area:
http://www.fairchildsemi.com/packing_dwg/PKG-ZA03F_BK.pdf

Physical Dimensions (Continued)

SOT-23

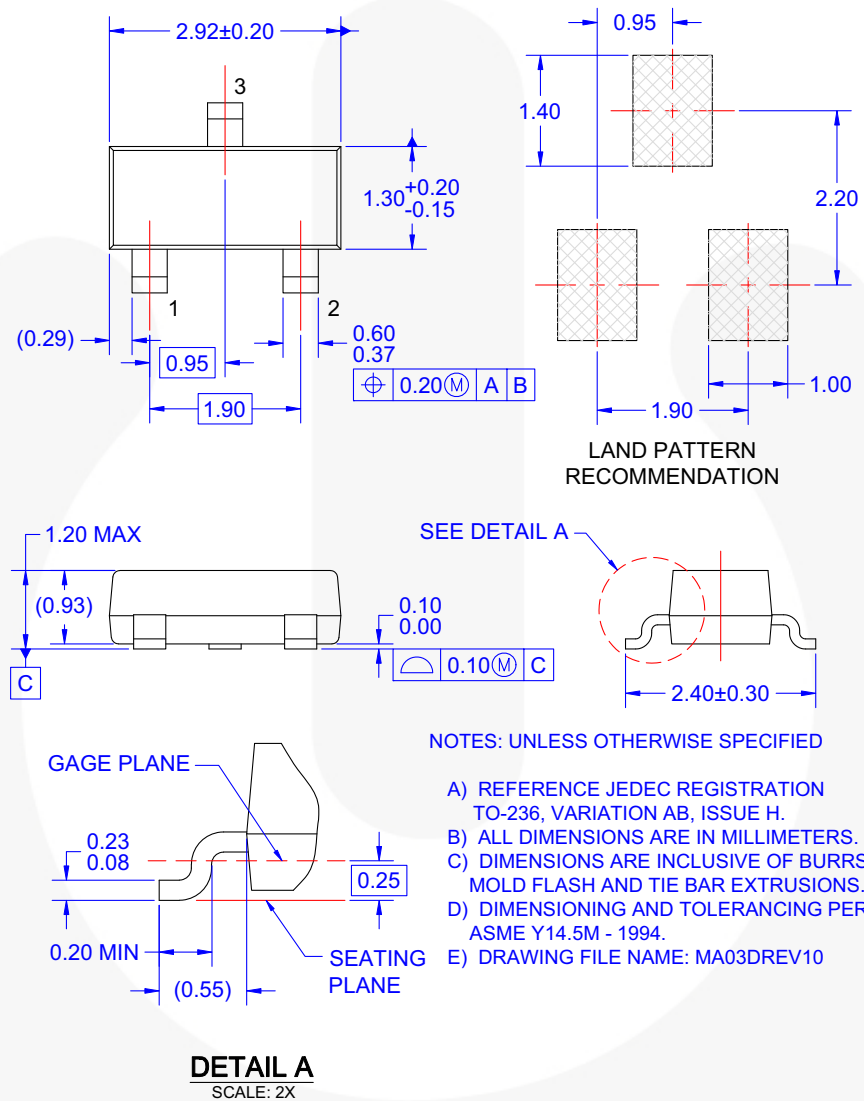


Figure 16. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE (ACTIVE)

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For current tape and reel specifications, visit Fairchild Semiconductor's online packaging area:
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Physical Dimensions (Continued)

SOT-223

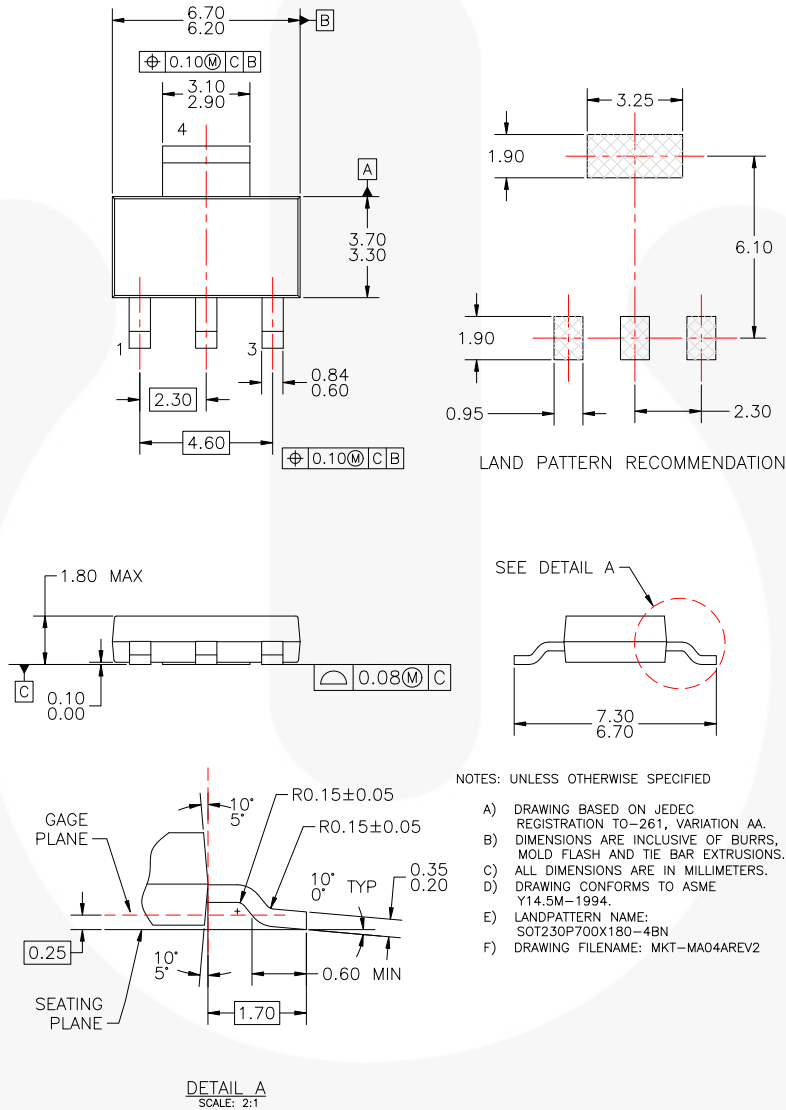


Figure 17. MOLDED PACKAGING, SOT-223, 4-LEAD (ACTIVE)

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MMBT2907A

PNP GENERAL PURPOSE SWITCHING TRANSISTOR

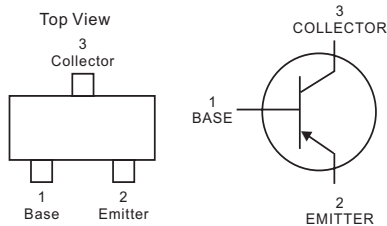
VOLTAGE 60 Volts **POWER** 225 mW

FEATURES

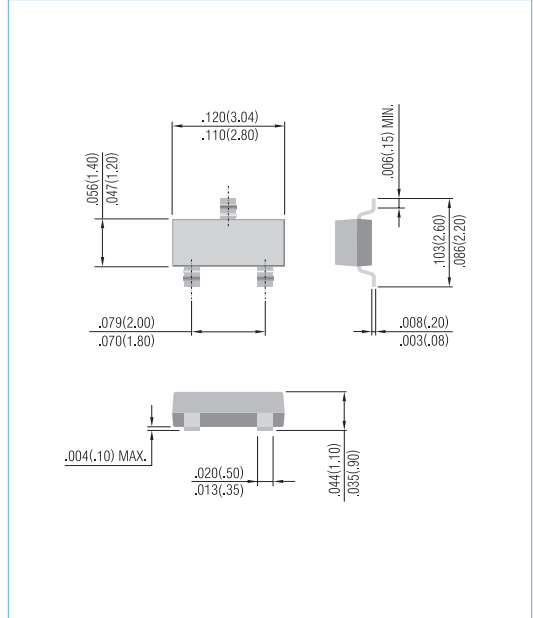
PNP epitaxial silicon, planar design
 Collector-emitter voltage $V_{CE} = -60V$
 Collector current $I_C = -600mA$
 In compliance with EU RoHS 2002/95/EC directives

MECHANICAL DATA

Case: SOT-23
 Terminals : Solderable per MIL-STD-750, Method 2026
 Approx Weight: 0.008 grams
 Device Marking : M7A



SOT-23 Unit: inch (mm)



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Units
Collector-Emitter Voltage	V_{CEO}	-60	V
Collector-Base Voltage	V_{CBO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-600	mA

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	225	mW
Storage Temperature	T_{STG}	-55 to 150	°C
Junction Temperature	T_J	-55 to 150	°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C / W

Note 1 : Transistor mounted on FR-4 board 70 x 60 x 1mm.



MMBT2907A

ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Collector-Emitter Breakdown Voltage	V _(BR) CEO	I _C =-10mA, I _B =0	-60	-	-	V
Collector-Base Breakdown Voltage	V _(BR) CBO	I _C =-10μA, I _E =0	-60	-	-	V
Emitter-Base Breakdown Voltage	V _(BR) EBO	I _E =-10μA, I _C =0	-5.0	-	-	V
Base Cutoff Current	I _{BL}	V _{CE} =-30V, V _{EB} =-0.5V	-	-	-50	nA
Collector Cutoff Current	I _{CEX}	V _{CE} =-30V, V _{EB} =-0.5V	-	-	-50	nA
	I _{CBO}	V _{CE} =-50V, I _E =0	-	-	-10	nA
		V _{CE} =-50V, I _E =0 T _J =125°C	-	-	-10	μA
DC Current Gain	h _{FE}	I _C =-0.1mA, V _{CE} =-10V I _C =-1.0mA, V _{CE} =-10V I _C =-10mA, V _{CE} =-10V I _C =-150mA, V _{CE} =-10V I _C =-500mA, V _{CE} =-10V	75 100 100 100 50	- - - - -	- - - 300 -	-
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-150mA, I _B =-15mA I _C =-500mA, I _B =-50mA	- -	- -	-0.4 -1.6	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =-150mA, I _B =-15mA I _C =-500mA, I _B =-50mA	- -	- -	-1.3 -2.6	V
Collector-Base Capacitance	C _{CB0}	V _{CB} =-10V, I _E =0, f=1MHz	-	-	8.0	pF
Emitter-Base Capacitance	C _{EBO}	V _{CB} =-2V, I _C =0, f=1MHz	-	-	30	pF
Current Gain-Bandwidth Product	F _T	I _C =-50mA, V _{CE} =-20V, f=100MHz	200	-	-	MHz
Turn-On Time	t _{on}	V _{CC} =-30V, V _{BE} =-0.5V, I _C =-150mA, I _B =-15mA	-	-	45	ns
Delay Time	t _d	V _{CC} =-30V, V _{BE} =-0.5V, I _C =-150mA, I _B =-15mA	-	-	10	ns
Rise Time	t _r	V _{CC} =-30V, V _{BE} =-0.5V, I _C =-150mA, I _{B1} =-15mA	-	-	40	ns
Turn-Off Time	t _{off}	V _{CC} =-6V, I _C =-150mA, I _{B1} =I _{B2} =-15mA	-	-	100	ns
Storage Time	t _s	V _{CC} =-6V, I _C =-150mA, I _{B1} =I _{B2} =-15mA	-	-	80	ns
Fall Time	t _f	V _{CC} =-6V, I _C =-150mA, I _{B1} =I _{B2} =-15mA	-	-	30	ns



MMBT2907A

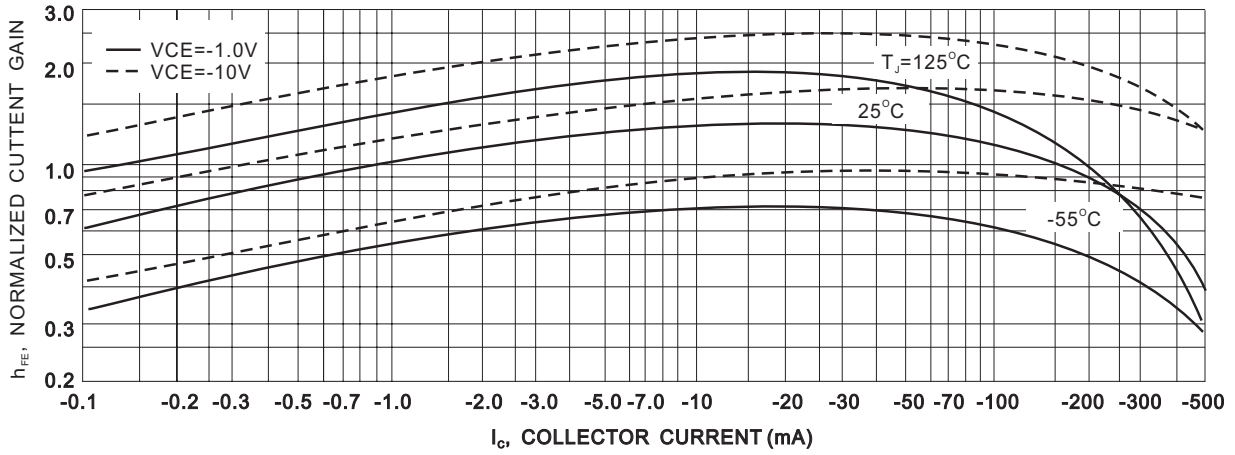


Fig.1-DC Current Gain

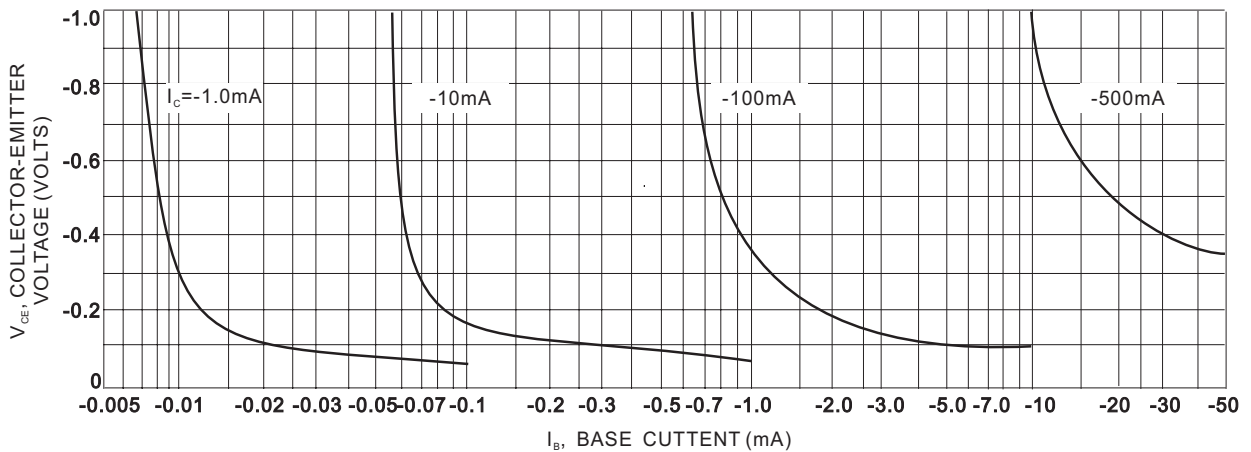


Fig.2-Collector Saturation Region

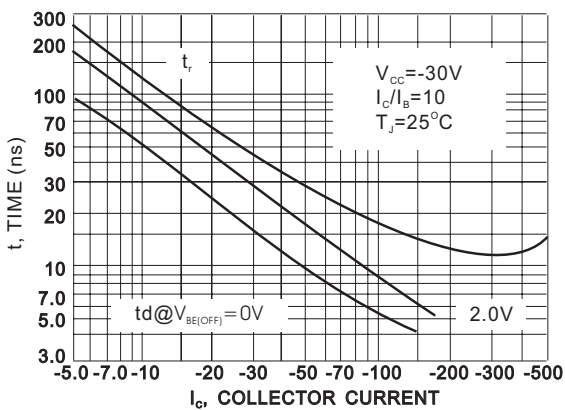


Fig.3-Turn-On Time

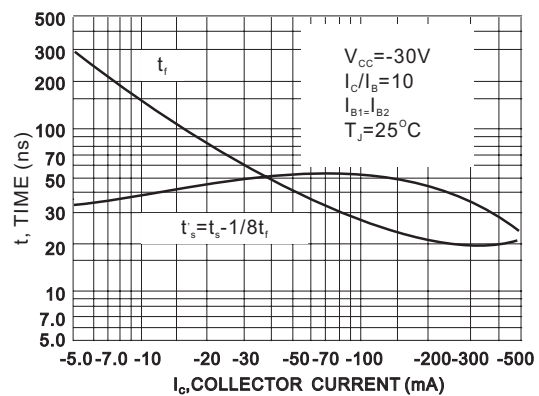
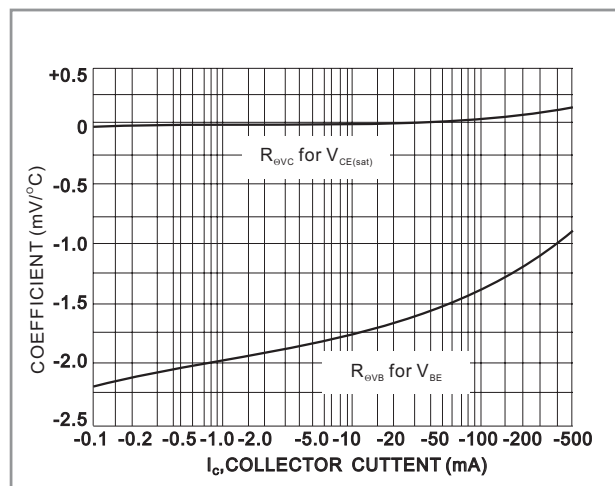
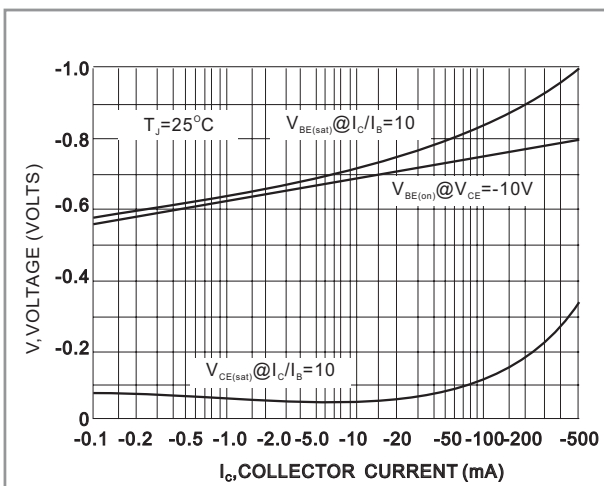
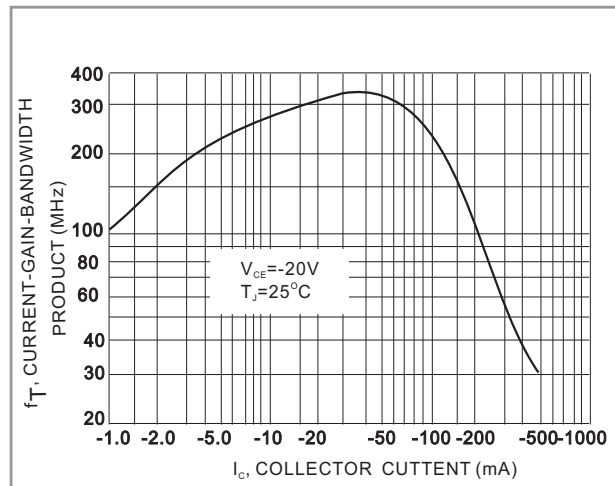
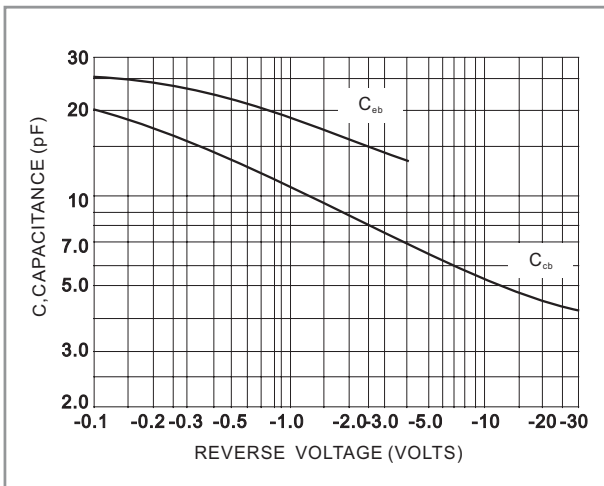
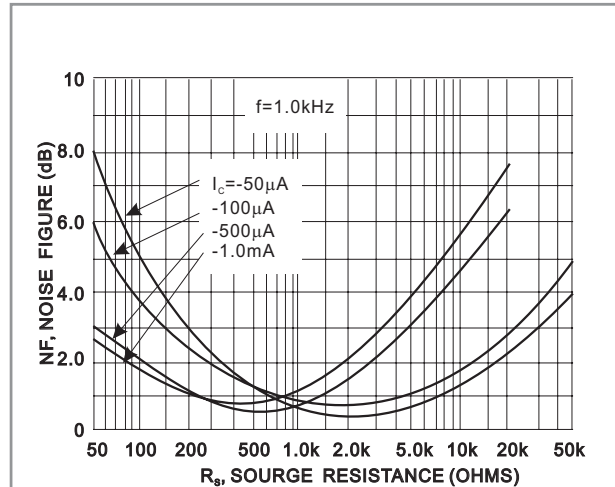
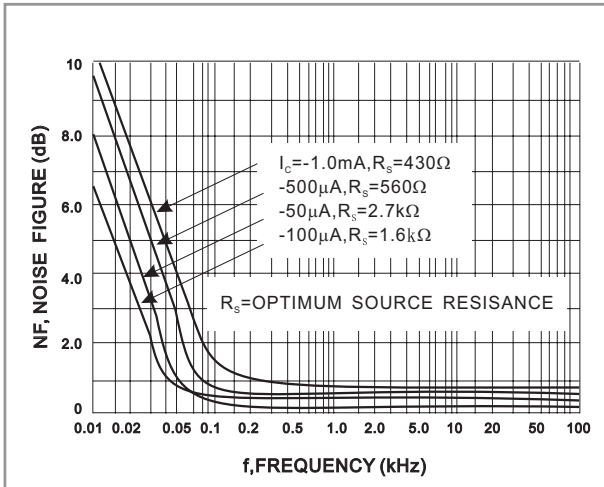


Fig.4-Turn-Off Time



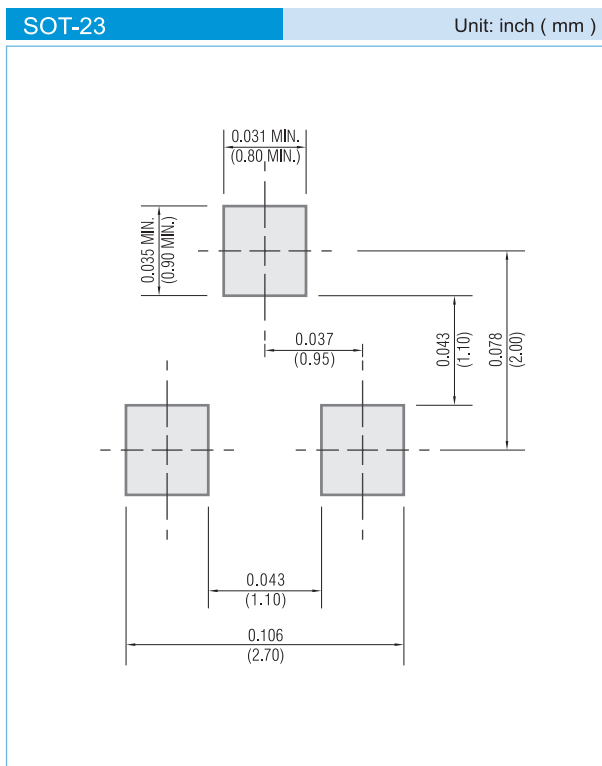
MMBT2907A





MMBT2907A

MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information
 - T/R - 12K per 13" plastic Reel
 - T/R - 3K per 7" plastic Reel

LEGAL STATEMENT

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